TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

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UHF TV TUNER RF AMPLIFIER APPLICATIONS

• Low Noise Figure : NF=4dB (Typ.)

• High Power Gain: Gpb=17dB (Typ.)

• Excellent Forward AGC Characteristics

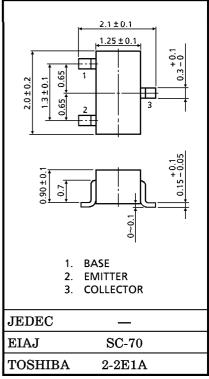
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	25	V
Collector-Emitter Voltage	v_{CEO}	20	V
Emitter-Base Voltage	$V_{ m EBO}$	2	V
Base Current	$I_{\mathbf{B}}$	4	mA
Collector Current	$I_{\mathbf{C}}$	20	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	100	mW
Junction Temperature	T_{j}	125	°C
Storage Temperature Range	$\mathrm{T}_{\mathrm{stg}}$	-55~125	°C

Marking



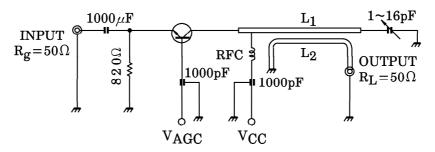
Unit in mm



Weight: 0.006g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

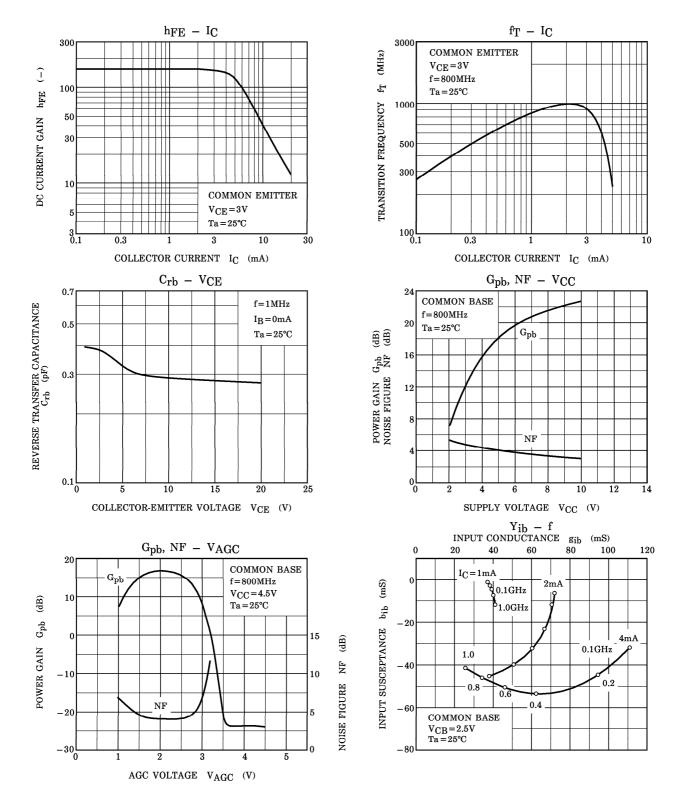
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 10V, I_{E} = 0$	_	_	0.1	μ A
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB}=2V, I_{C}=0$	_	_	1	μ A
Collector Emitter Breakdown Voltage	V _(BR) CEO	$I_{C}=1$ mA, $I_{B}=0$	20	_	_	V
DC Current Gain	$h_{ ext{FE}}$	$V_{CE}=3V, I_{C}=1mA$	40	100	_	_
Transition Frequency	${ m f_T}$	$V_{CE}=3V, I_{C}=1mA$	500	850	_	MHz
Reverse Transfer Capacitance	$C_{ m rb}$	$V_{CE} = 2V, I_{B} = 0, f = 1MHz$	_	0.4	0.55	pF
Power Gain	$G_{ m pb}$	$V_{CC}=4.5V, V_{AGC}=2V$	12	17	_	dB
Noise Figure	NF	f=800MHz (Fig.1)	_	4	6	dB
AGC Voltage	VAGC	V _{CC} =4.5V, G.R.=-20dB, f=800MHz	2.5	3.2	4.0	V

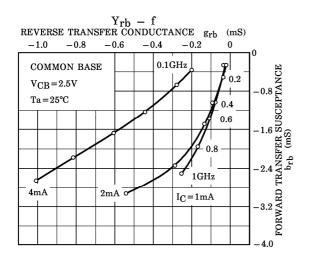


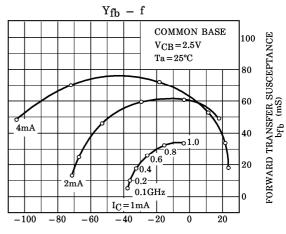
 L_1 , L_2 : ϕ 1.0mm SILVER PLATED COPPER WIRE

(Note) VAGC measured by the test circuit shown in Fig.1, when the power gain is reduced to 20dB compared with Gpb shown above Table.

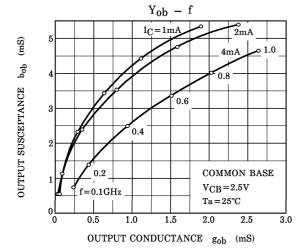
Fig.1 800MHz Gpb, NF TEST CIRCUIT

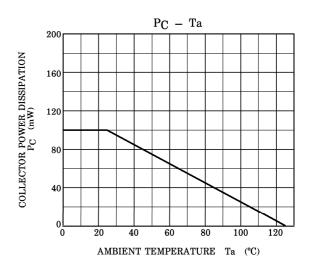






FORWARD TRANSFER CONDUCTANCE g_{fb} (mS)





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